NSN 5961-01-036-1226

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-036-1226 **Inclosure Material:** Metal **Overall Length:** Between 0.896 inches and 0.936 inches **Overall Diameter:** 2.000 inches **Mounting Facility Quantity: Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1200.0 repetitive peak reverse voltage and 1200.0 repetitive peak off-state voltage and 1300.0 nonrepetitive peak off-state voltage **Current Rating Per Characteristic:** 7000.00 amperes forward current, total rms watts **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Mtg facilities included **Terminal Type And Quantity:** 2 insulated wire lead w/terminal lug and 2 electron tube base Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0